

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau



Rec'd PCT/PTO 00 000 2005

(43) International Publication Date
22 January 2004 (22.01.2004)

PCT

(10) International Publication Number
WO 2004/008506 A1

(51) International Patent Classification⁷: H01L 21/02,
21/205, C30B 29/36, C03B 29/06

(21) International Application Number:
PCT/JP2003/008312

(22) International Filing Date: 30 June 2003 (30.06.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
2002-202953 11 July 2002 (11.07.2002) JP

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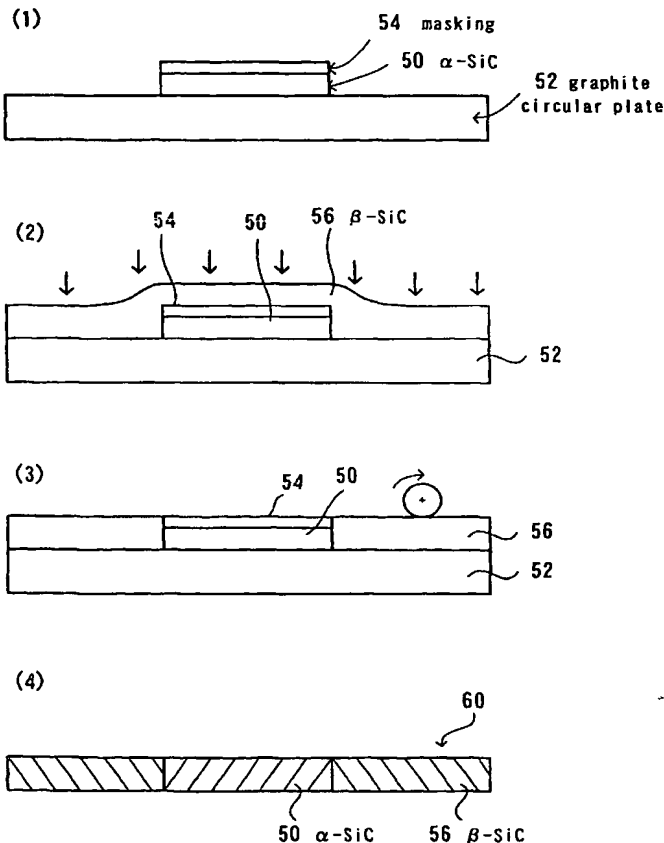
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(81) Designated States (national): AE, AG, AL, AM, AT, AU,
AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU,
CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH,
GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC,
LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW,
MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC,
SD, SE, SG, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG,
US, UZ, VC, VN, YU, ZA, ZM, ZW.

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(54) Title: LARGE-DIAMETER SIC WAFER AND MANUFACTURING METHOD THEREOF



(57) **Abstract:** From the viewpoint of manufacturing an SiC semiconductor device economically, a present Si device manufacturing line is utilized to make it possible to handle a small-diameter SiC wafer. Polycrystal SiC is grown from at least one surface side of a small-diameter α -SiC single crystal wafer so as to be in a size of an outer diameter corresponding to a handling device of an existing semiconductor manufacturing line, and thereafter the polycrystal SiC on the surface of the α -SiC single crystal wafer is ground to manufacture an increased-diameter SiC of a double structure in which the polycrystal SiC is grown around an outer circumference of the small-diameter α -SiC single crystal wafer.